

Description

The AR3321D5 is a low capacitance TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3321D5 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with ±20kV air and ±20kV contact discharge. It is assembled into a SOD-523 lead-free package. The small size and high ESD surge protection make AR3321D5 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

Ultra low capacitance: 0.3pF typical

Ultra low leakage: nA levelOperating voltage: 3.3V

Low clamping voltage

Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±20kV Contact discharge: ±20kV

- IEC61000-4-5 (Lightning) 4A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOD-523

Case Material: "Green" Molding Compound.

Terminal Connections: See Diagram Below

• Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

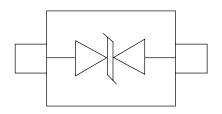
Marking Information



35: Device Marking Code

Ordering Information

Circuit and Pin Configuration



Circuit and Pin Schematic

Part Number	Packaging	Reel Size	
AR3321D5	3000/Tape & Reel	7 inch	



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

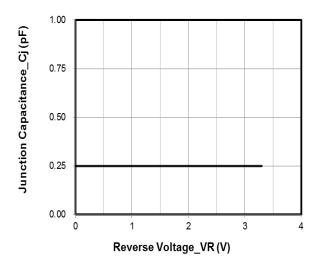
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	100	W
Peak Pulse Current (8/20µs)	IPP	4	А
ESD per IEC 61000-4-2 (Air)	\/505	±20	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±20	
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

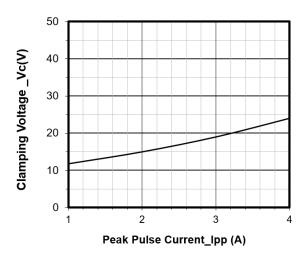
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Breakdown Voltage	VBR	5			V	IT = 1mA
Reverse Leakage Current	I _R			0.2	μA	VRWM = 3.3V
Clamping Voltage	Vc			12	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			25	V	IPP = 4A (8 x 20µs pulse)
Junction Capacitance	СЛ		0.3		pF	VR = 0V, f = 1MHz



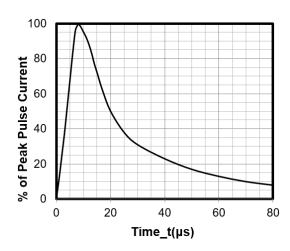
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



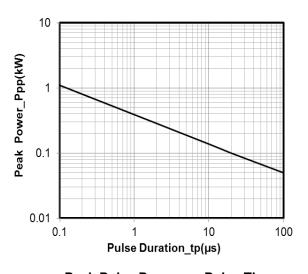
Junction Capacitance vs. Reverse Voltage



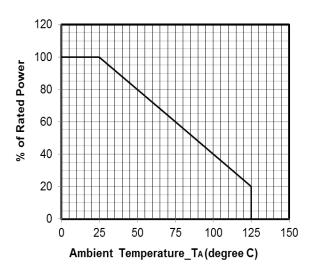
Clamping Voltage vs. Peak Pulse Current



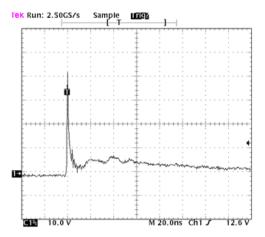
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



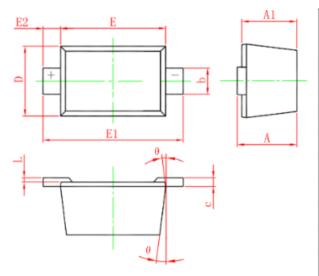
Power Derating Curve



Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

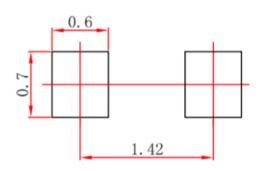


SOD-523 Package Outline Drawing



	DIMENSIONS								
	MILLIMETERS			INCHES					
SYM	MIN	NOM	MAX	MIN	NOM	MAX			
Α	0.51		0.77	0.020		0.031			
A1	0.50		0.70	0.020		0.028			
b	0.25		0.35	0.010		0.014			
С	0.08		0.15	0.003		0.006			
D	0.75		0.85	0.030		0.033			
Е	1.10		1.30	0.043		0.051			
E1	1.50		1.70	0.059		0.067			
E2	0.20REF			0.008REF					
L	0.01		0.07	0.001		0.003			
Θ	7° REF			7° REF					

Suggested Land Pattern



Unit: mm

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